TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX04FT,TC74VCX04FK

Low-Voltage Hex Inverter with 3.6-V Tolerant Inputs and Outputs

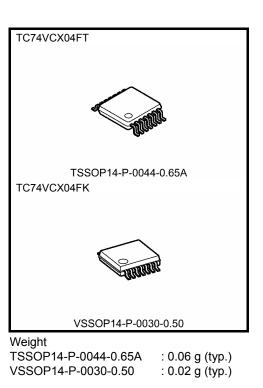
The TC74VCX04FT/FK is a high-performance CMOS inverter which is guaranteed to operate from 1.2-V to 3.6-V. Designed for use in 1.5V, 1.8V, 2.5V or 3.3V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

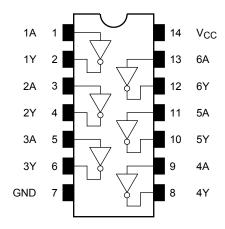
All inputs are equipped with protection circuits against static discharge.

Features (Note)

- Low-voltage operation: VCC = 1.2~3.6 V
- High-speed operation : $t_{pd} = 2.8 \text{ ns} (\text{max}) (V_{CC} = 3.0 \sim 3.6 \text{ V})$
 - $t_{pd} = 3.7 \text{ ns} (\text{max}) (V_{CC} = 2.3 \sim 2.7 \text{ V})$
 - $t_{pd} = 7.4 \text{ ns} (\text{max}) (V_{CC} = 1.65 \sim 1.95 \text{ V})$
 - $t_{pd} = 14.8 \text{ ns} (\text{max}) (\text{V}_{CC} = 1.4 \sim 1.6 \text{ V})$
 - $t_{pd} = 37.0 \text{ ns} (max) (V_{CC} = 1.2 \text{ V})$
- Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA} \text{ (min)} (V_{CC} = 3.0 \text{ V})$
 - $: I_{OH}/I_{OL} = \pm 18 \text{ mA} (\text{min}) (V_{CC} = 2.3 \text{ V})$
 - $: I_{OH}/I_{OL} = \pm 6 \text{ mA (min)} (V_{CC} = 1.65 \text{ V})$ $: I_{OH}/I_{OL} = \pm 2 \text{ mA (min)} (V_{CC} = 1.4 \text{ V})$
 - \cdot 10H/10L ± 2 mA (min) (Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200$ V
 - Human body model $\geq \pm 200$ V
- Package: TSSOP and VSSOP (US)
- Power-down protection provided on all inputs and outputs



Pin Assignment (top view)



IEC Logic Symbol

1A <u>1</u>	1	<u>2</u> 1Y
2A <u>3</u>		4 2Y
3A <u>5</u>		6 3Y
4A <u>9</u>		8 4Y
5A <u>11</u>		<u>10</u> 5Y
6A <u>13</u>		12 6Y

Truth Table

Inputs	Outputs
А	Y
L	Н
Н	L

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V _{IN}	-0.5~4.6	V	
DC output voltage	Vour	-0.5~4.6 (Note 2)	V	
De output voltage	Vout	-0.5~V _{CC} + 0.5(Note 3)	v	
Input diode current	I _{IK}	-50	mA	
Output diode current	IOK	±50 (Note 4)	mA	
DC output current	IOUT	±50	mA	
Power dissipation	PD	180	mW	
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA	
Storage temperature	T _{stg}	-65~150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: $V_{CC} = 0 V$

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	1.2~3.6	V
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	Vour	0~3.6 (Note 2)	V
Output voltage	Vout	0~V _{CC} (Note 3)	v
		±24 (Note 4)	
Output current	IOH/IOL	±18 (Note 5)	mA
Output current	'OH/'OL	±6 (Note 6)	ША
		±2 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: $V_{CC} = 0 V$

Note 3: High or low state

Note 4:	$V_{CC} = 3.0 \sim 3.6 V$
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- Note 5: $V_{CC} = 2.3 \sim 2.7 \text{ V}$
- Note 6: $V_{CC} = 1.65 \sim 1.95 \text{ V}$
- Note 7: $V_{CC} = 1.4 \sim 1.6 V$
- Note 8: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = -40 to 85° C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics		Symbol	Test (Condition		Min	Мах	Unit
Charaoter	101100	Cymbol			$V_{CC}(V)$	IVIIII	Max	Onic
Input voltage	H-level	VIH		_	2.7~3.6	2.0		V
input voltage	L-level	VIL		_	2.7~3.6		0.8	v
H-level			I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	_		
	VOH	$V_{IN} = V_{IL}$	I _{OH} = -12 mA	2.7	2.2			
				I _{OH} = -18 mA	3.0	2.4		
				I _{OH} = -24 mA	3.0	2.2		V
			V _{IN} = V _{IH}	I _{OL} = 100 μA	2.7~3.6	_	0.2	
	L-level	Va		I _{OL} = 12 mA	2.7	_	0.4	
	L-level	V _{OL}		I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V		2.7~3.6	_	±5.0	μA
Power-off leakage	current	IOFF	V_{IN} , $V_{OUT} = 0$ to 3.6 V		0	_	10.0	μA
	Surront	Icc	$V_{IN} = V_{CC}$ or GND		2.7~3.6		20.0	
Quiescent supply t	Quiescent supply current		$V_{CC} \leq V_{IN} \leq 3.6 \text{ V}$		2.7~3.6		±20.0	μA
Increase in I _{CC} per	rinput	∆lcc	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6		750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics		Symbol	Test (Condition		Min	Max	Unit
		Symbol	Test Condition		V _{CC} (V)	IVIIII	IVIAX	Onit
Input voltage	H-level	VIH		_	2.3~2.7	1.6		V
input voltage	L-level	VIL			2.3~2.7		0.7	v
			I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_		
	H-level	VOH	$V_{IN} = V_{IL}$	$I_{OH} = -6 \text{ mA}$	2.3	2.0		V
				I _{OH} = -12 mA	2.3	1.8	_	
Output voltage				I _{OH} = -18 mA	2.3	1.7	_	
			$V_{IN} = V_{IH}$	$I_{OL} = 100 \ \mu A$	2.3~2.7		0.2	
	L-level	V _{OL}		$I_{OL} = 12 \text{ mA}$	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6	
Input leakage curre	ent	I _{IN}	$V_{IN} = 0$ to 3.6 V		2.3~2.7		±5.0	μA
Power-off leakage	current	I _{OFF}	V_{IN} , $V_{OUT} = 0$ to 3.6 V		0		10.0	μA
Quiescent supply c	urrent	loo	$V_{IN} = V_{CC}$ or GND	$V_{IN} = V_{CC}$ or GND			20.0	μA
Quiescent supply c	unent	Icc	$V_{CC} \leqq V_{IN} \leqq 3.6 \text{ V}$		2.3~2.7		±20.0	μΑ

DC Characteristics (Ta = –40 to 85°C, 1.65 V \leq V_{CC} < 2.3 V)

Characteristics		Symbol	Test Co	ondition		Min	Max	Unit
		0,1120			$V_{CC}(V)$		Max	U
	H-level	VIH	_	_	1.65~2.3	$\begin{array}{c} 0.65 \times \\ V_{CC} \end{array}$		V
Input voltage	L-level	VIL	_		1.65~2.3	_	$0.2 \times V_{CC}$	v
н	H-level	H-level V _{OH}	$V_{IN} = V_{IL}$	I _{OH} = -100 μA	1.65~2.3	V _{CC} - 0.2		
Output voltage				I _{OH} = -6 mA	1.65	1.25	_	V
· -	L-level	Max		$I_{OL} = 100 \ \mu A$	1.65~2.3	_	0.2	
	L-IEVEI	V _{OL}	$V_{IN} = V_{IH}$	I _{OL} = 6 mA	1.65	_	0.3	
Input leakage curre	nt	I _{IN}	V _{IN} = 0 to 3.6 V		1.65~2.3	_	±5.0	μA
Power-off leakage of	current	IOFF	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μA
Quiescent supply c	O dia sector and a sector at		$V_{IN} = V_{CC}$ or GND		1.65~2.3		20.0	
Quiescent supply c		Icc	$V_{CC} \leq V_{IN} \leq 3.6 \text{ V}$		1.65~2.3		±20.0	μA

DC Characteristics (Ta = –40 to 85°C, 1.4 V \leq V_{CC} < 1.65 V)

Characteristics		Symbol	Test C	ondition		Min	Мах	Unit
		Symbol	Test C	Test Condition		IVIIII	IVIAA	Onit
Input voltage	H-level	VIH	-	—	1.4~1.65	$0.65 \times V_{CC}$	_	V
L-level	L-level	VIL	—		1.4~1.65	_	$0.05 \times V_{CC}$	v
ŀ	H-level	Voh	V _{IN} = V _{IL}	I _{OH} = -100 μA	1.4~1.65	V _{CC} - 0.2	_	v
Output voltage				$I_{OH} = -2 \text{ mA}$	1.4	1.05	_	
	L-level	V _{OL}		I _{OL} = 100 μA	1.4~1.65	_	0.05	
		VOL	$V_{IN} = V_{IH}$ $I_{OL} = 2 \text{ mA}$		1.4	—	0.35	
Input leakage curre	ent	I _{IN}	$V_{IN} = 0$ to 3.6 V		1.4~1.65	—	±5.0	μA
Power-off leakage	current	I _{OFF}	V_{IN} , $V_{OUT} = 0$ to 3.6 V		0	—	10.0	μA
Quiescent supply current		$V_{IN} = V_{CC}$ or GND		1.4~1.65	_	20.0	μA	
Quiescent supply c	unent	Icc	$V_{CC} \stackrel{\scriptstyle \leq}{=} V_{IN} \stackrel{\scriptstyle \leq}{=} 3.6 \ V$		1.4~1.65	_	±20.0	μA

DC Characteristics (Ta = -40 to 85°C, 1.2 V \leq V_{CC} < 1.4 V)

Characteris	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	VIH	_	_	1.2~1.4	$0.8 \times V_{CC}$	_	V
input voitage	L-level	VIL	_		1.2~1.4		$\begin{array}{c} 0.05 \times \\ V_{CC} \end{array}$	v
Output voltage	H-level	V _{OH}	$V_{IN} = V_{IL}$	V _{IN} = V _{IL} I _{OH} = -100 μA		V _{CC} - 0.1	_	V
	L-level	V _{OL}	$V_{IN} = V_{IH}$	I _{OL} = 100 μA	1.2	_	0.05	
Input leakage currer	nt	I _{IN}	$V_{IN} = 0$ to 3.6 V		1.2		±5.0	μA
Power-off leakage c	urrent	IOFF	V_{IN} , $V_{OUT} = 0$ to 3.6 V		0	_	10.0	μA
Quiescent supply cu	Quies and a mark a summat		$V_{IN} = V_{CC}$ or GND		1.2		20.0	
Quescent supply ct		Icc	$V_{CC} \leq V_{IN} \leq 3.6 \text{ V}$		1.2		±20.0	μA

AC Characteristics (Ta = -40 to 85°C, input: $t_r = t_f = 2.0$ ns) (Note 1)

Characteristics	Symbol	Test 0	Test Condition			Max	Unit
				V _{CC} (V)			
			CL = 15 pF, RL = 2 kΩ	1.2	3.0	37.0	
	tau		ο _μ = 10 μι, τι <u>μ</u> = 2 κω	1.5 ± 0.1	2.0	14.8	
Propagation delay time	t _{pLH} t _{pHL}	Figure 1, Figure 2		$\textbf{1.8} \pm \textbf{0.15}$	1.5	7.4	ns
	φnc		$C_L = 30 \text{ pF}, \text{ R}_L = 500 \Omega$	2.5 ± 0.2	0.8	3.7	
				$\textbf{3.3}\pm\textbf{0.3}$	0.6	2.8	
			$C_L = 15 \text{ pF}, R_L = 2 \text{ k}\Omega$	1.2		1.5	
	+			1.5 ± 0.1		1.5	
Output to output skew	t _{osLH}	(Note 2)		1.8 ± 0.15	_	0.5	ns
	t _{osHL}		$C_L = 30 \text{ pF}, \text{ R}_L = 500 \Omega$	2.5 ± 0.2		0.5	
				$\textbf{3.3}\pm\textbf{0.3}$		0.5	

Note 1: For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design. $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, \ t_{osHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$)

Characteristics	Symbol	Test Condition		1	Тур.	Unit
	Cymbol			$V_{CC}(V)$		
		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	0.25	
Quiet output maximum dynamic V_{OL}	V _{OLP}	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	0.8	
	V _{OLV}	$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	-0.25	
Quiet output minimum dynamic V_{OL}		$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	-0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	-0.8	
		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	1.5	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	—		1.8, 2.5, 3.3	6	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$	(Note)	1.8, 2.5, 3.3	20	pF

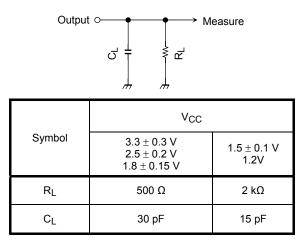
Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 (per gate)$

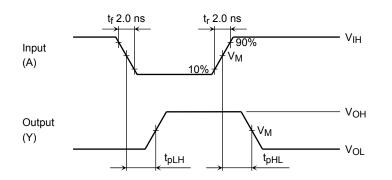
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AC Test Circuit





AC Waveform



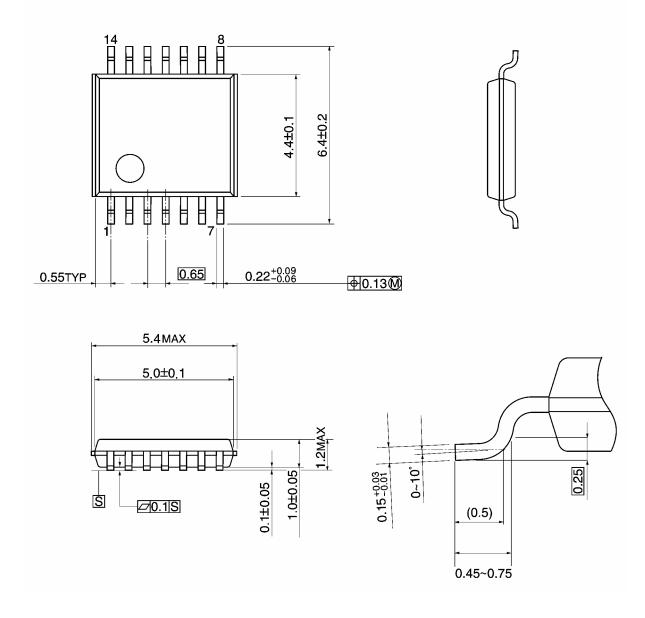
Symbol	V _{CC}								
Symbol	$3.3\pm0.3~V$	$2.5\pm0.2\;V$	$1.8\pm0.15~V$	$1.5\pm0.1~\text{V}$	1.2 V				
VIH	2.7 V	V _{CC}	V _{CC}	V _{CC}	V _{CC}				
VM	1.5 V	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2				

Figure 2 t_{pLH}, t_{pHL}

Package Dimensions

TSSOP14-P-0044-0.65A

Unit: mm



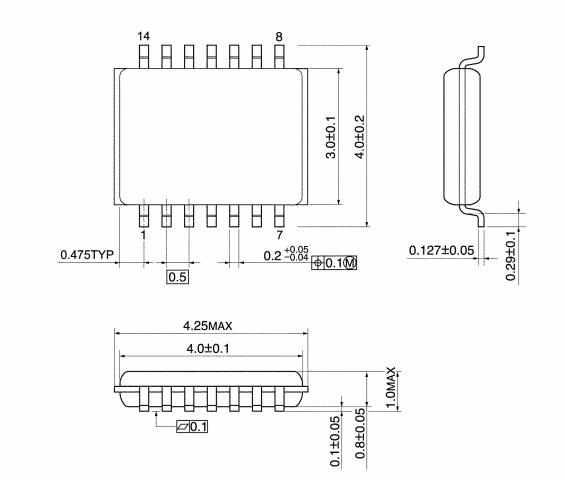
Weight: 0.06 g (typ.)

TOSHIBA

Package Dimensions

VSSOP14-P-0030-0.50

Unit: mm



Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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